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CHOI(10) **Pub. No.: US 2014/0097411 A1**(43) **Pub. Date: Apr. 10, 2014**(54) **ORGANIC LIGHT-EMITTING DISPLAY
DEVICE AND METHOD OF
MANUFACTURING THE SAME**(52) **U.S. CL.**CPC **H01L 51/5203** (2013.01)USPC **257/40; 438/34**(71) Applicant: **Chaun-Gi CHOI**, Yongin-City,
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Gyeonggi-Do (KR)(21) Appl. No.: **13/833,818**(22) Filed: **Mar. 15, 2013**(30) **Foreign Application Priority Data**

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(2006.01)

(57) **ABSTRACT**

An organic light-emitting display device may include a plurality of scan lines, a plurality of data lines, and a plurality of pixels located at an intersection region of the scan line and the data line, wherein the organic light-emitting display device includes a thin film transistor including a gate electrode on a different layer than a scan line, an active layer on the gate electrode, and source and drain electrodes that are in contact with source and drain regions of the active layer, and a capacitor including a first capacitor electrode on the same layer as the scan line, a second capacitor electrode on the gate electrode, and a third electrode on the same layer as the source and drain electrodes.

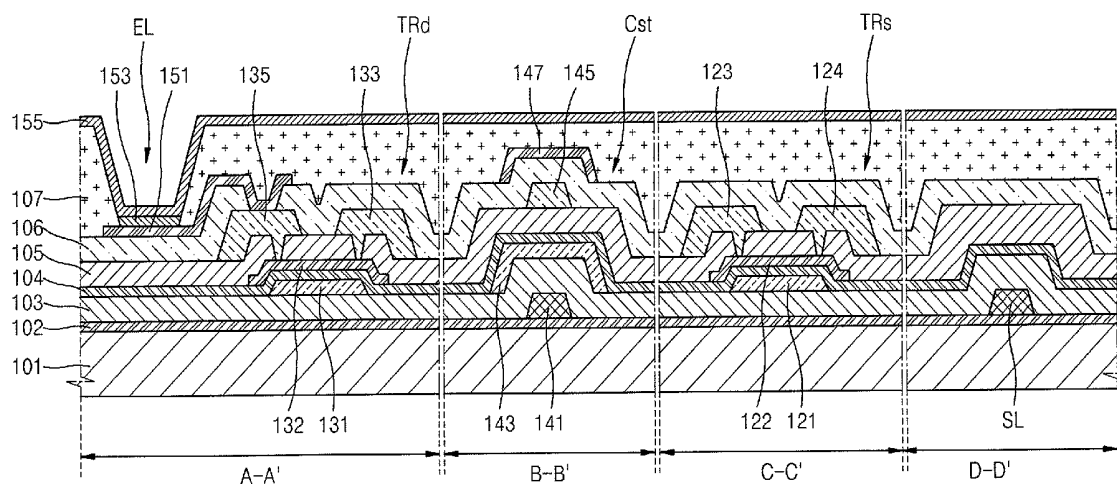


FIG. 2

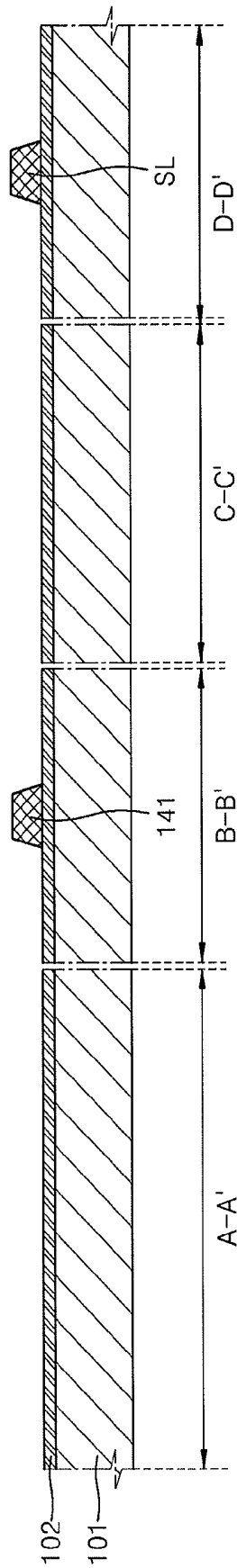


FIG. 3

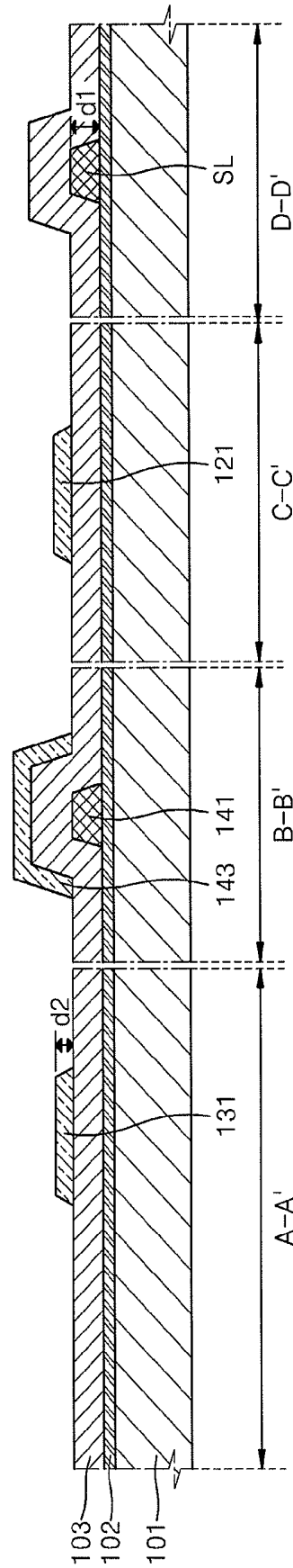


FIG. 4

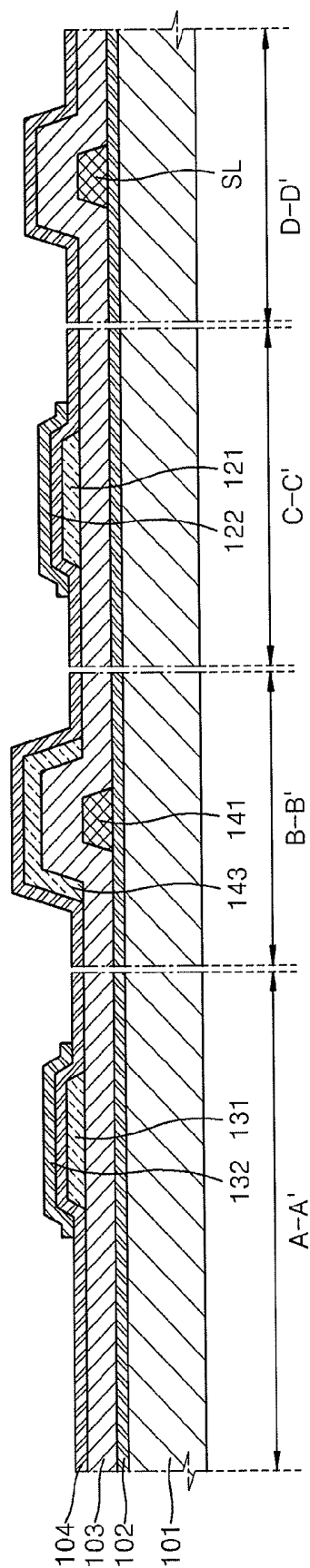


FIG. 5

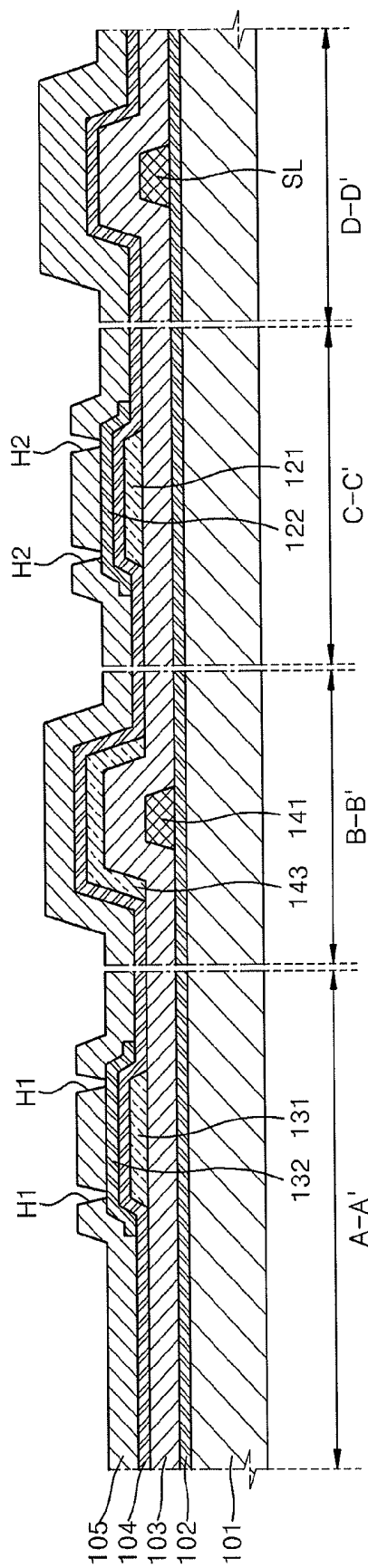


FIG. 6

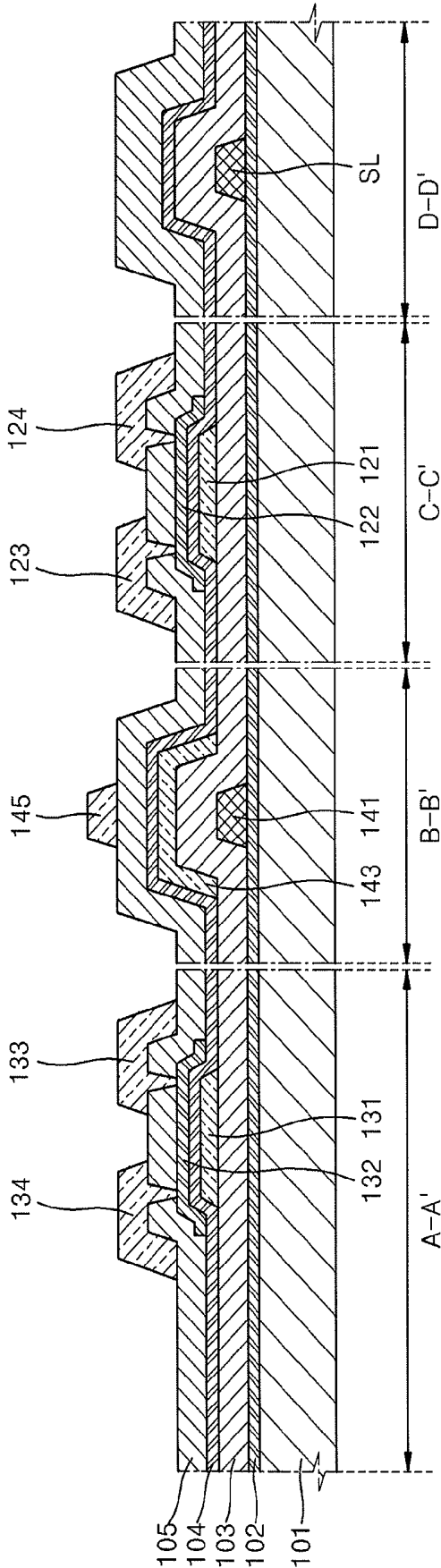


FIG. 7

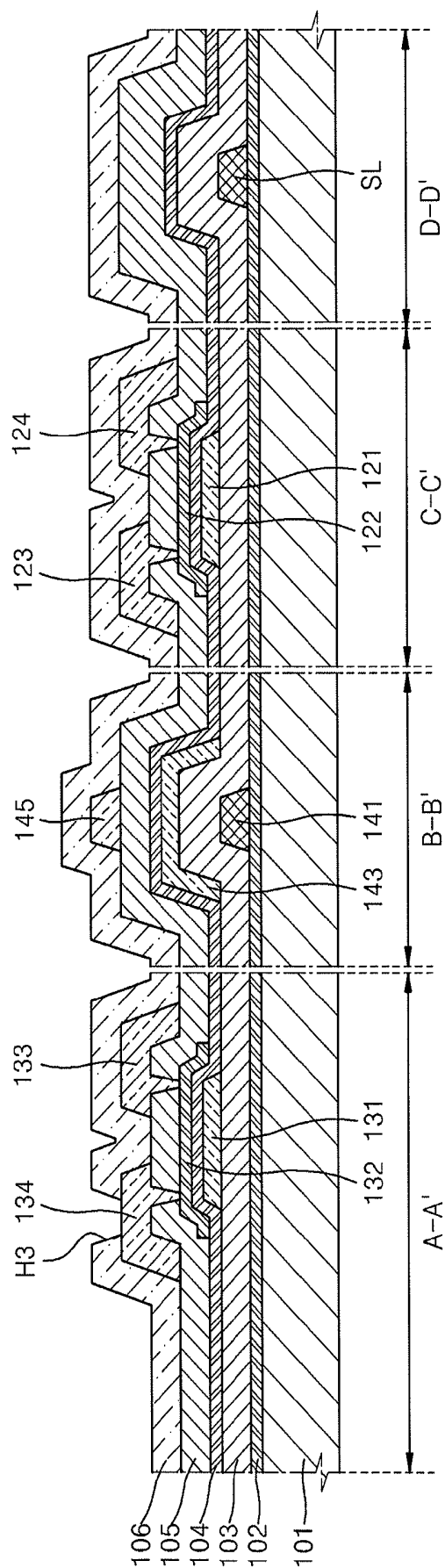


FIG. 8

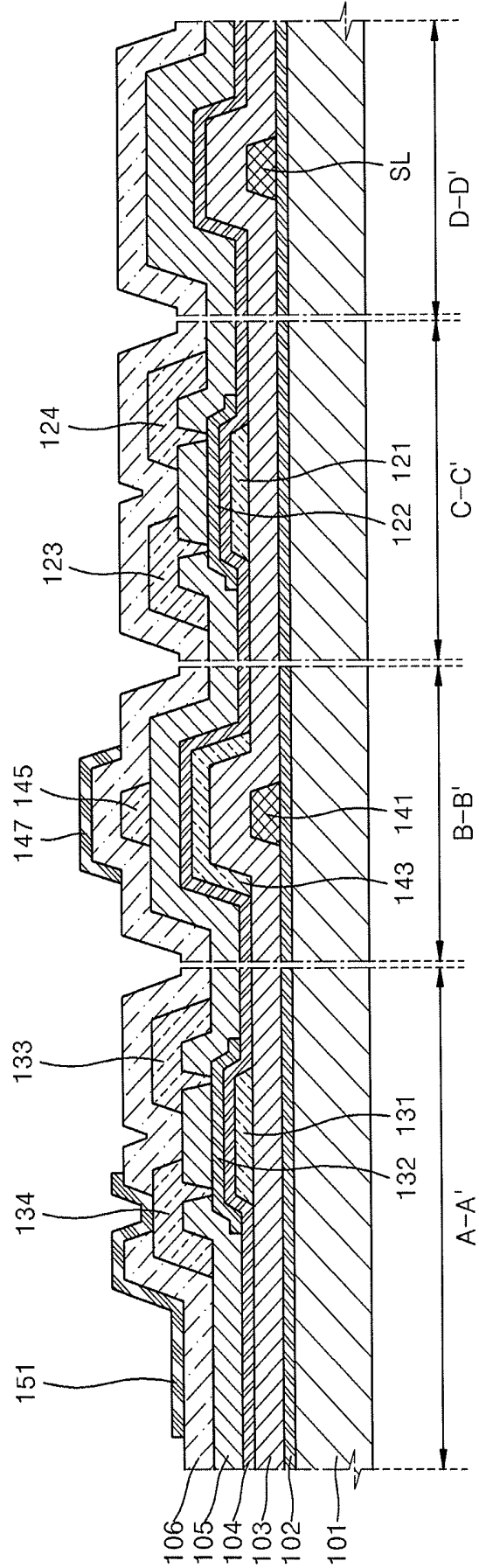


FIG. 9

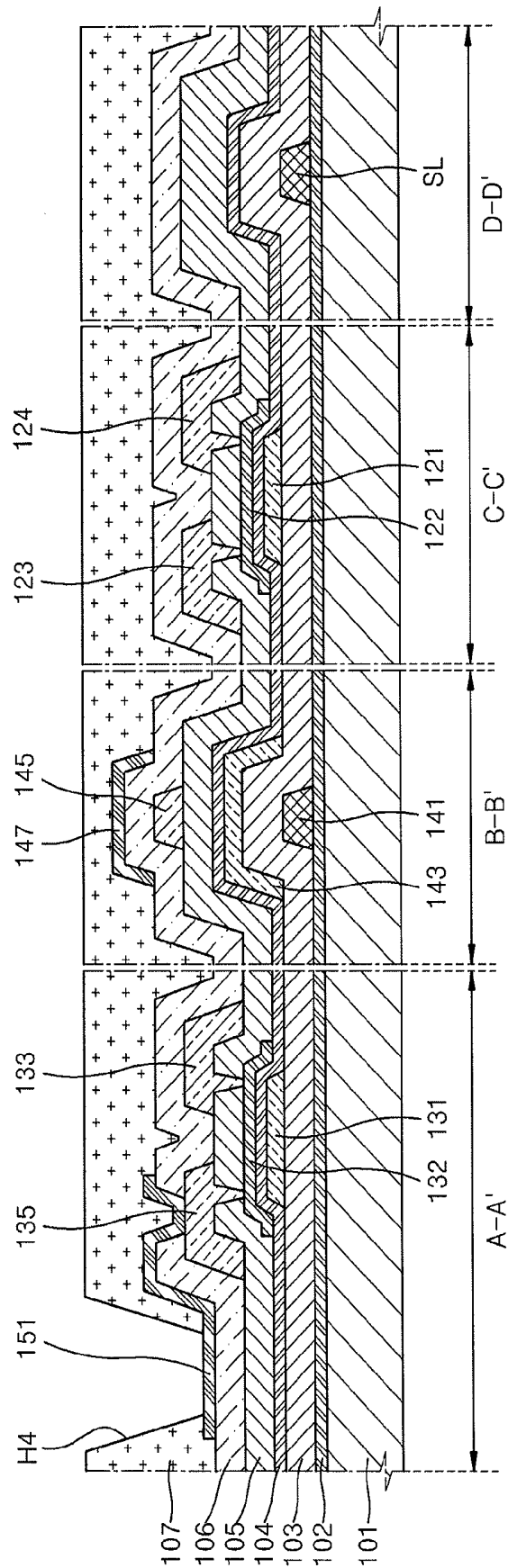


FIG. 10

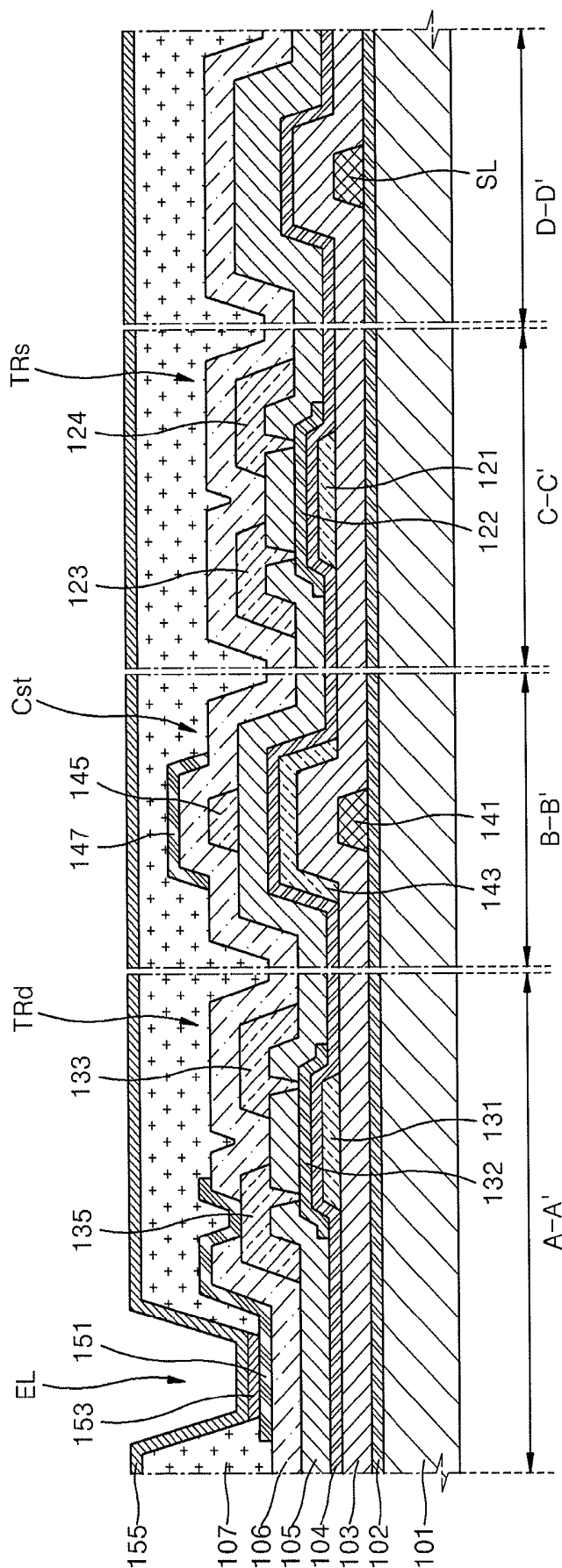


FIG. 11

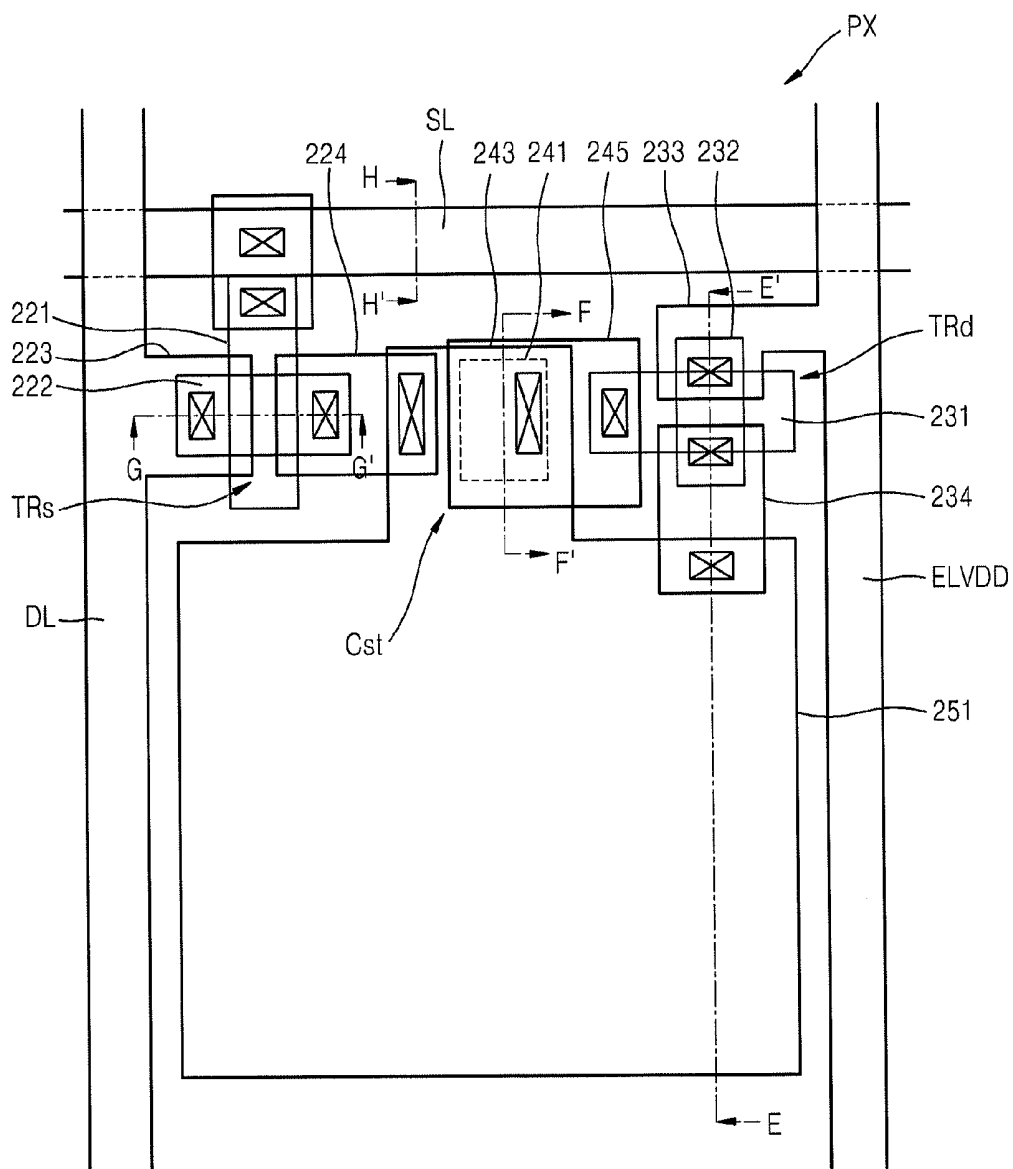


FIG. 12

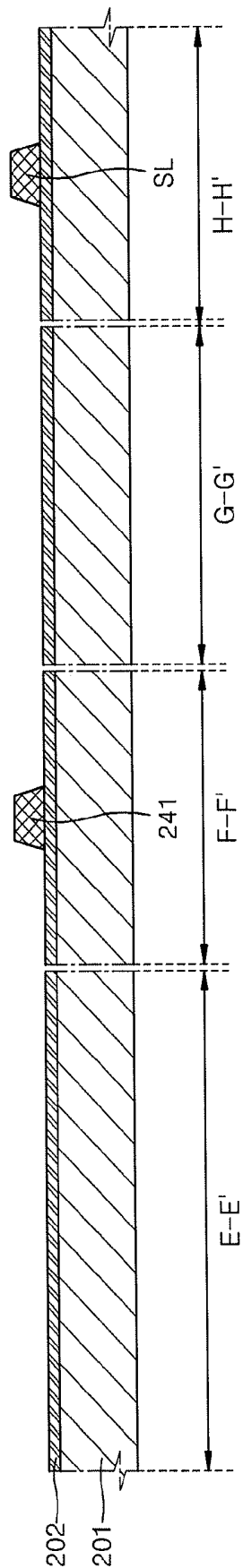


FIG. 13

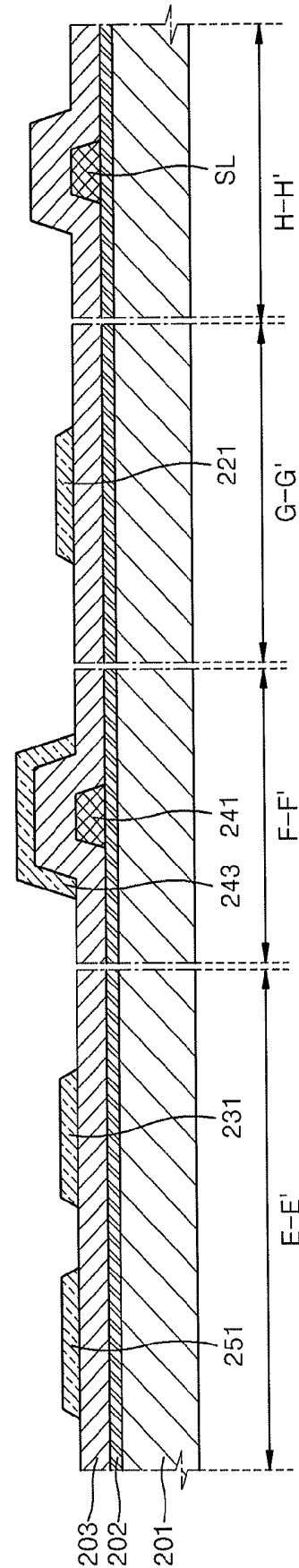


FIG. 14

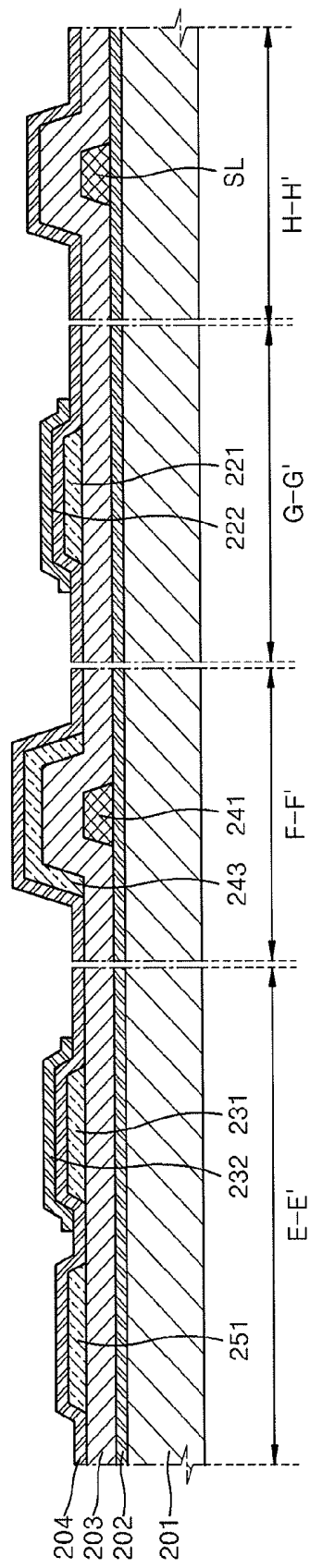


FIG. 15

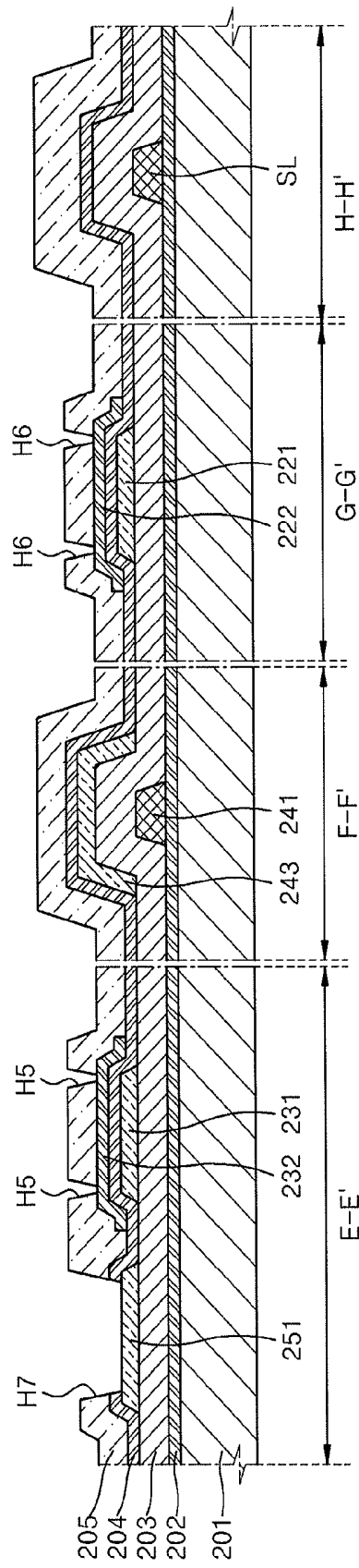


FIG. 16

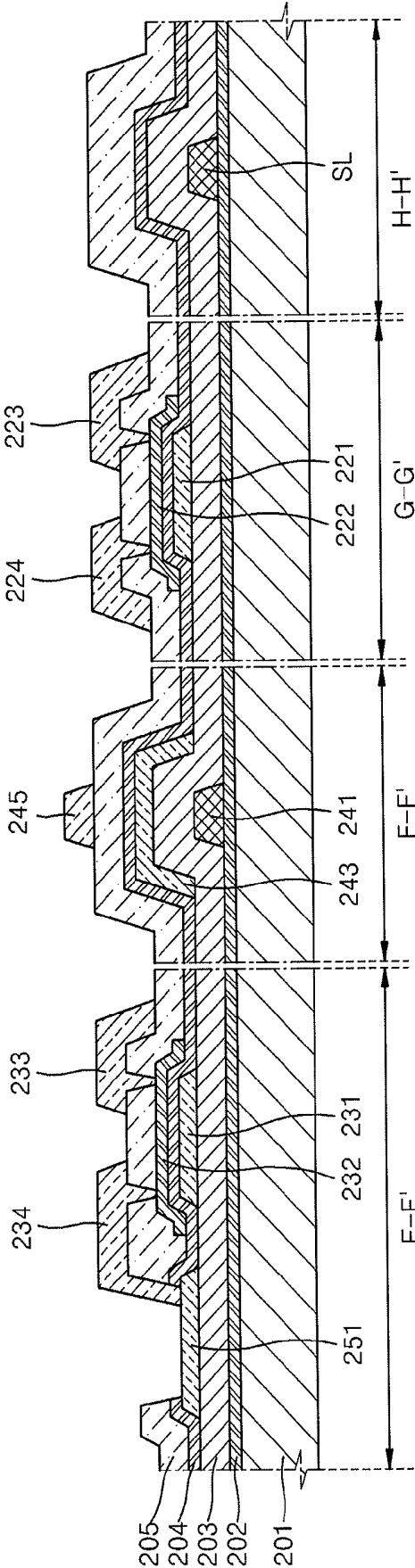


FIG. 17

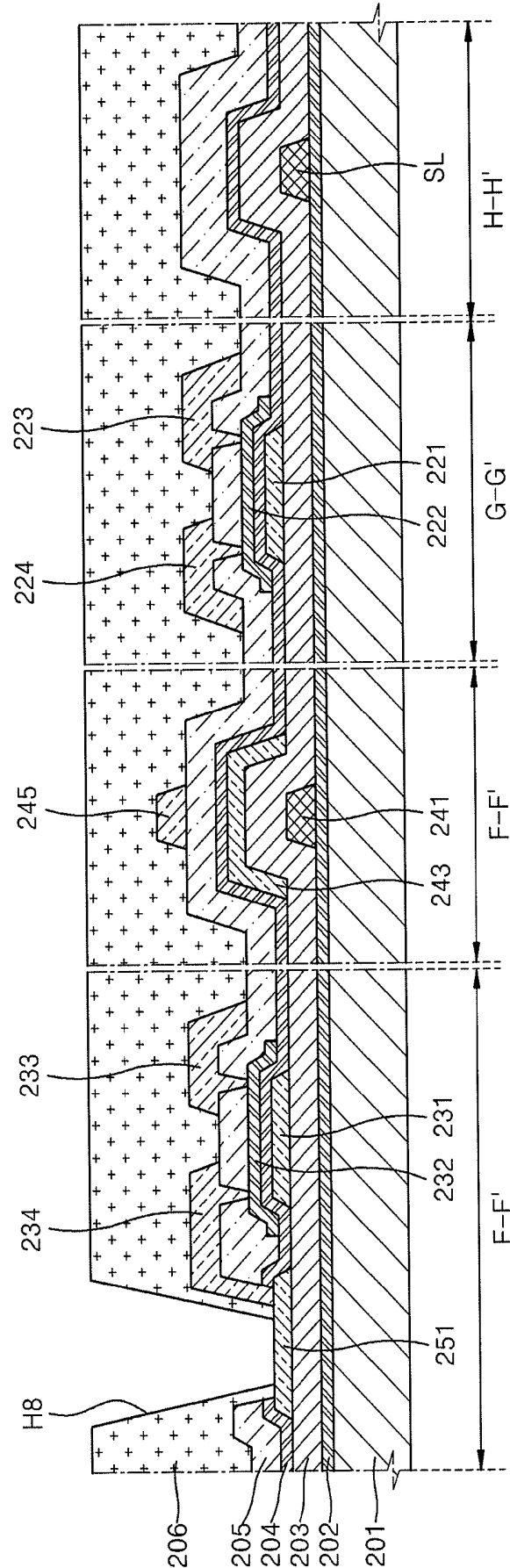
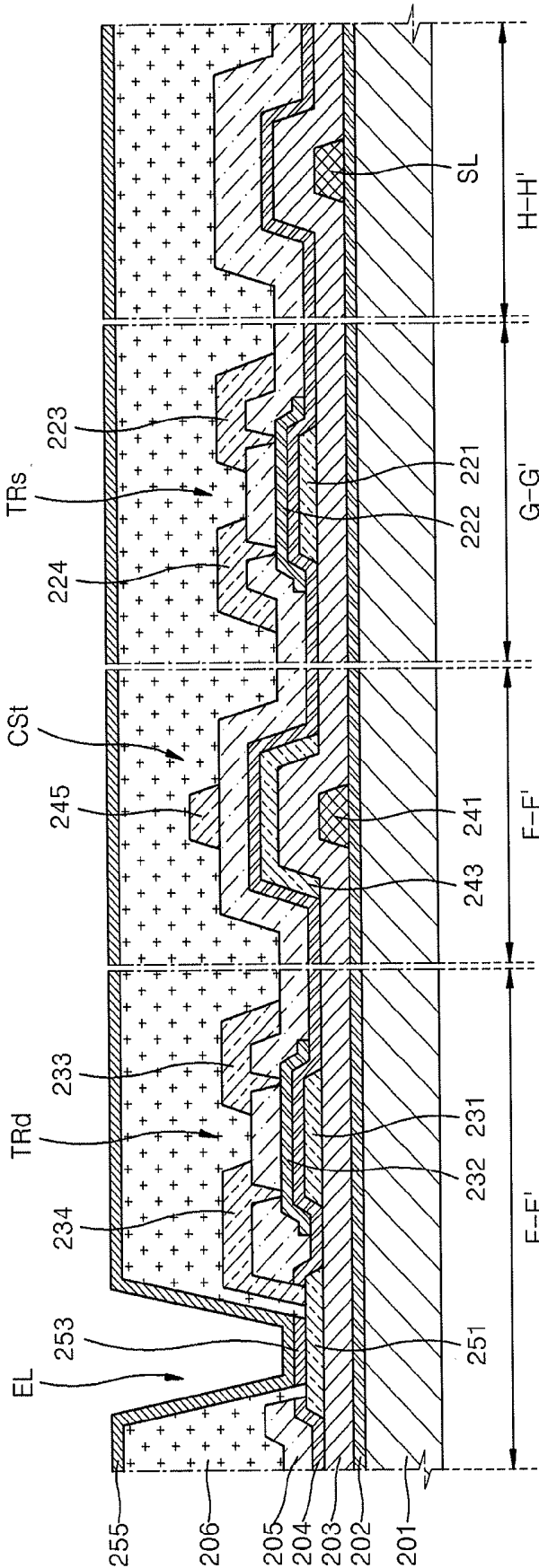


FIG. 18



ORGANIC LIGHT-EMITTING DISPLAY DEVICE AND METHOD OF MANUFACTURING THE SAME

CROSS-REFERENCE TO RELATED PATENT APPLICATION

[0001] This application claims priority under 35 U.S.C. 119 to and the benefit of Korean Patent Application No. 10-2012-0112084, filed on Oct. 9, 2012, in the Korean Intellectual Property Office, the disclosure of which is incorporated herein in its entirety by reference.

BACKGROUND

[0002] 1. Field of the Invention

[0003] Embodiments relate to an organic light-emitting display device and a method of manufacturing the same.

[0004] 2. Description of the Related Art

[0005] Flat panel display devices, such as organic light-emitting display devices or liquid crystal display devices, include a plurality of pixels including thin film transistors (TFTs), capacitors, and wiring connecting the TFTs and capacitors.

[0006] Each pixel of an organic light-emitting display device having TFTs receives signals through scan lines and data lines for transmitting scan signals and data signals, and emits lights using power lines for supplying power to each pixel.

[0007] However, the scan lines, data lines, and power lines are wires formed of metal, thus the signals supplied to pixels placed far from where the signals are supplied may be distorted due to line resistance. Therefore, a luminance of the organic light-emitting display device may be uneven, and accordingly, a reliability of the organic light-emitting display device may be decreased.

SUMMARY

[0008] One or more embodiments is directed to providing an organic light-emitting display device including a plurality of scan lines and a plurality of data lines, and a plurality of pixels each located at an intersection region of the scan line and the data line, wherein the organic light-emitting display device includes a thin film transistor including a gate electrode disposed on a different layer than a scan line, an active layer on the gate electrode, and source and drain electrodes in contact with source and drain regions of the active layer; and a capacitor including a first capacitor electrode disposed on a same layer as the scan line, a second capacitor electrode disposed on the gate electrode, and a third capacitor electrode disposed on the same layer as the source and drain electrodes.

[0009] The active layer may be formed of an oxide semiconductor.

[0010] A thickness of the gate electrode may be thinner than a thickness of the scan line, and the scan line may be a low resistance wire.

[0011] The capacitor may further include a fourth capacitor electrode disposed on the third capacitor electrode. The organic light-emitting display device may further include a first insulating layer disposed between the first capacitor electrode and the second capacitor electrode, a second insulating layer and a third insulating layer disposed between the second capacitor electrode and the third capacitor electrode, and a fourth insulating layer disposed between the third capacitor electrode and the fourth capacitor electrode.

[0012] The organic light-emitting display device may further include a pixel electrode disposed on the source and drain electrodes and on the same layer as the fourth capacitor electrode.

[0013] The organic light-emitting display device may further include a pixel electrode disposed on the same layer as the gate electrode and the second capacitor electrode. Also, the organic light-emitting display device may further include a first insulating layer disposed between the first capacitor electrode and the second capacitor electrode, and a second insulating layer and a third insulating layer disposed between the second capacitor electrode and the third capacitor electrode.

[0014] The scan line and the gate electrode may be electrically connected through contact holes formed in an insulating layer between the scan line and the gate electrode.

[0015] One or more embodiments is directed to providing a method of manufacturing an organic light-emitting display device, the method including forming a first capacitor electrode on the same layer as a scan line; forming a first insulating layer on the first capacitor electrode and forming a gate electrode and a second capacitor electrode on the first insulating layer; forming a second insulating layer on the gate electrode and the second capacitor electrode and forming an active layer which overlaps with the gate electrode on the second insulating layer; forming a third insulating layer including openings, which expose a part of source and drain regions of the active layer, in the active layer; and forming a third capacitor and forming source and drain electrodes that are in contact with the source and drain regions through the openings, on the third insulating layer.

[0016] The active layer may be formed of an oxide semiconductor.

[0017] A thickness of the gate electrode may be thinner than a thickness of the scan line. Also, the scan line may be a low resistance wire.

[0018] The method may further include forming a fourth insulating layer on the source and drain electrodes and forming a fourth capacitor electrode on the fourth insulating layer. The method may further include forming a pixel electrode on the same layer as the fourth capacitor electrode. Also, the method may further include forming a fifth insulating layer, which has an opening that exposes a part of the pixel electrode, on the pixel electrode and the fourth capacitor electrode.

[0019] The method may further include forming the pixel electrode on the same layer as the gate electrode and the second capacitor electrode. The method may further include forming a fourth insulating layer, which has an opening that exposes a part of the pixel electrode, on the pixel electrode, which is partially exposed by the opening included in the second insulating layer and the third insulating layer, the third capacitor electrode, and the source and drain electrodes.

[0020] The method may further include forming an electrode pattern that electrically connects the scan line and the gate electrode through contact holes formed in an insulating layer between the scan line and the gate electrode.

BRIEF DESCRIPTION OF THE DRAWINGS

[0021] The above and other features will become more apparent by describing in detail exemplary embodiments thereof with reference to the attached drawings in which:

[0022] FIG. 1 is a plan view of a single pixel of an organic light-emitting display device according to an embodiment;

[0023] FIGS. 2 to 10 are cross-sectional views of FIG. 1 cut through lines A-A', B-B', C-C', and D-D' to describe stages in a method of manufacturing the organic light-emitting display device, according to an embodiment;

[0024] FIG. 11 is a plan view of a single pixel of an organic light-emitting display device according to another embodiment; and

[0025] FIGS. 12 to 18 are cross-sectional views of FIG. 11 cut through lines E-E', F-F', G-G', and H-H' to describe stages in a method of manufacturing the organic light-emitting display device, according to an embodiment.

DETAILED DESCRIPTION

[0026] As used herein, the term “and/or” includes any and all combinations of one or more of the associated listed items.

[0027] Hereinafter, the exemplary embodiments according will be described in detail with reference to the accompanying drawings.

[0028] Like reference numerals refer to like elements. In the description, if it is determined that a detailed description of commonly-used technologies or structures related to the invention may unnecessarily obscure the subject matter, the detailed description will be omitted.

[0029] In the drawings, the thicknesses of layers and regions are exaggerated for clarity. It will also be understood that when a layer is referred to as being “on” another layer or substrate, it can be directly on the other layer or substrate, or intervening layers may also be present.

[0030] FIG. 1 is a plan view of a single pixel of an organic light-emitting display device according to an embodiment.

[0031] The organic light-emitting display device according to an embodiment includes a plurality of scan lines SL and a plurality of data lines DL on a substrate 101, and a plurality of pixels PX each located at an intersection region of the scan line SL and the data line DL. Referring to FIG. 1, each of the pixels PX includes an organic light-emitting diode for realizing colors in response to a data signal, a driving transistor TRd for applying driving current according to the data signal to the organic light-emitting diode, a switching transistor TRs that turns on/off the driving transistor TRd by transmitting the data signal according to a scan signal, and a capacitor Cst for storing voltage that corresponds to the data signal. Here, the pixel PX may further include a plurality of thin film transistors TFTs and capacitors to compensate for a threshold voltage of the driving transistor TRd.

[0032] The switching transistor TRs includes a gate electrode 121 on a layer above the scan line SL, an active layer 122 on the gate electrode 121, and source and drain electrodes 123 and 124 that are electrically connected to two terminal ends of the active layer 122 through contact holes. The gate electrode 121 is electrically connected to the scan line SL through contact holes. One of the source and drain electrodes 123 and 124 are electrically connected to the data line DL and the other is electrically connected to a second capacitor electrode 143 of the capacitor Cst through contact holes. One of the source and drain electrodes 123 and 124 that is electrically connected to the data line DL may be extended from and integrated with the data line DL.

[0033] The driving transistor TRd includes a gate electrode 131 on a layer above the scan line SL, an active layer 132 on the gate electrode 131, and source and drain electrodes 133 and 134 that are electrically connected to the two terminal ends of the active layer 132 through contact holes. The gate electrode 131 is electrically connected to a third capacitor

electrode 145 of the capacitor Cst through contact holes. One of the source and drain electrodes 133 and 134 is electrically connected to a driving voltage supply line ELVDD, and the other is electrically connected to a pixel electrode 151 of the organic light-emitting diode EL through contact holes. One of the source and drain electrodes 133 and 134 that is electrically connected to the driving voltage supply line ELVDD may extend from and may be integrated with the driving voltage supply line ELVDD.

[0034] The capacitor Cst includes a first capacitor electrode 141 on the same layer as the scan line SL, a second capacitor electrode 143 on the first capacitor electrode 141 and formed on the same layer as the gate electrodes 121 and 131, a third capacitor electrode 145 on the second capacitor electrode 143 and formed on the same layer as the source and drain electrodes 123 and 124 and 133 and 134, and a fourth capacitor electrode 147 on the third capacitor electrode 145 and formed on the same layer as the pixel electrode 151 of the organic light-emitting diode EL. The first capacitor electrode 141 and the third capacitor electrode 145 are electrically connected through contact holes. The fourth capacitor electrode 147 may be extended from and integrated with the pixel electrode 151.

[0035] FIGS. 2 to 10 are cross-sectional views of FIG. 1 cut through lines A-A', B-B', C-C', and D-D' to describe a stages in a method of manufacturing the organic light-emitting display device, according to an embodiment.

[0036] Referring to FIG. 2, a buffer layer 102 is formed on the substrate 101, a first mask (not shown) is formed on the buffer layer 102, and the scan line SL and the first capacitor electrode 141 of the capacitor Cst are formed on the buffer layer 102 by masking with a first mask (not shown).

[0037] The substrate 101 may be formed of a transparent glass material, mainly including SiO₂. However, the substrate 101 of the present embodiment is not limited thereto, and may be formed of various materials such as, e.g., transparent plastic material or metal material.

[0038] The buffer layer 102 serves as a barrier layer and/or a blocking layer to prevent diffusion of impurity ions and permeation of moisture or external air, and to planarize a surface of the substrate 101. The buffer layer 102 may be formed using SiO₂ and/or SiN_x by various deposition methods, such as plasma enhanced chemical vapor deposition (PECVD), atmospheric pressure chemical vapor deposition (APCVD), and low pressure chemical vapor deposition (LPCVD).

[0039] The scan line SL and the first capacitor electrode 141 may be formed simultaneously by stacking a first conductive layer on the substrate 101 and patterning the first conductive layer. The first conductive layer includes at least one metal material in the group of aluminum (Al), platinum (Pt), palladium (Pd), silver (Ag), magnesium (Mg), gold (Au), nickel (Ni), neodymium (Nd), iridium (Ir), chromium (Cr), lithium (Li), calcium (Ca), molybdenum (Mo), titanium (Ti), tungsten (W), and copper (Cu). The first conductive layer may be formed as a single layer or multiple layers. A first conductive layer may include a metal material with a low resistance, such as Al or Cu, but the first conductive layer may include other metal materials to form the first conductive layer as a single layer or multiple layers with an increased thickness.

[0040] Next, as shown in FIG. 3, a first insulating layer 103 is formed on the substrate 101, and then, the gate electrode 131 of the driving transistor TRd, the gate electrode 121 of the

switching transistor TRs, and the second capacitor electrode **143** of the capacitor Cst are formed on the first insulating layer **103** by masking with a second mask (not shown). The second capacitor electrode **143** overlaps the first capacitor electrode **141**. In particular, the second capacitor electrode **143** may be wider than the first capacitor electrode **141** to entirely overlap the first capacitor electrode **141**.

[0041] The first insulating layer **103** may be formed of at least one organic insulation material selected from the group of polyimide, polyamide, acrylic resin, benzocyclobutene, and phenol resin, or at least one inorganic insulation material selected from the group of SiO_2 , SiN_x , Al_2O_3 , CuO_x , Tb_4O_7 , Y_2O_3 , Nb_2O_5 , and Pr_2O_3 . Also, the first insulating layer **103** may include alternating layers of organic insulation materials and inorganic insulation materials.

[0042] The gate electrodes **121** and **131** and the second capacitor electrode **143** may be formed simultaneously by depositing the second conductive layer on the first insulating layer **103** and patterning the second conductive layer.

[0043] The second conductive layer includes at least one metal material selected from the group of aluminum (Al), platinum (Pt), palladium (Pd), silver (Ag), magnesium (Mg), gold (Au), nickel (Ni), neodymium (Nd), iridium (Ir), chromium (Cr), lithium (Li), calcium (Ca), molybdenum (Mo), titanium (Ti), tungsten (W), and copper (Cu), and the second conductive layer may be formed as a single layer or multiple layers. The second conductive layer may include at least one transparent conductive material selected from the group of indium tin oxide (ITO), indium zinc oxide (IZO), zinc oxide (ZnO), indium oxide (In_2O_3), indium gallium oxide (IGO), and aluminum zinc oxide (AZO). A thickness d2 of the second conductive layer may be thinner than a thickness d1 of the first conductive layer. Thus, the thickness d2 of the gate electrodes **121** and **131** is thinner than the thickness d1 of the scan line SL.

[0044] Referring to FIG. 4, the active layers **122** and **132** are formed on the gate electrodes **121** and **131** by masking with a third mask (not shown).

[0045] The second insulating layer **104** and an oxide semiconductor are deposited on the substrate **101**, on which the gate electrodes **121** and **131** and the first capacitor electrode **141** are formed, and then, the oxide semiconductor is patterned to form the active layers **122** and **132**. The active layers **122** and **132** each provide a channel region, a source region, and a drain region, wherein the channel region overlaps the gate electrodes **121** and **131**.

[0046] The second insulating layer **104** serves as a gate insulating layer and may be formed of an inorganic insulation material, such as SiN_x or SiO_x , or an organic insulation material. According to an embodiment, the scan line SL formed by the first conductive layer and the gate electrodes **121** and **131** formed by the second conductive layer may be formed apart, the gate electrodes **121** and **131** may be thinner than the scan line SL, which is a wire with low resistance. Thus, a thickness of the second insulating layer **104** may also be thin. Therefore, a size of a TFT may be reduced.

[0047] A TFT including the oxide semiconductor has excellent device characteristics and is processable at a low temperature. Thus, such a TFT is considered as an optimal device in a backplane for a flat panel display. In addition, the TFT including the oxide semiconductor is transparent within a band of visible light and flexible, thus the TFT may be used in a transparent display device or a flexible display device. The oxide semiconductor may contain at least one element

selected from the group of gallium (Ga), indium (In), stannum (Sn), zirconium (Zr), hafnium (Hf), and vanadium (V). For example, the oxide semiconductor may include at least one selected from the group of ZnO , SnO_2 , In_2O_3 , Zn_2SnO_4 , Ga_2O_3 , and HfO_2 . Also, the active layer **132** may be formed of a transparent oxide semiconductor. Examples of the transparent oxide semiconductor include, for example, Zn oxide, Sn oxide, Ga—In—Zn oxide, In—Zn oxide, and In—Sn oxide, but are not limited thereto.

[0048] Referring to FIG. 5, a third insulating layer **105** is stacked on the active layers **122** and **132**, and openings H1 and H2 exposing a part of the source and drain regions of the active layers **122** and **132** are formed by masking with a fourth mask (not shown).

[0049] The third insulating layer **105** serves as an inter-layer dielectric and may be formed of an inorganic insulation material, such as SiN_x or SiO_x , or an organic insulation material.

[0050] Next, referring to FIG. 6, the source electrodes **123** and **133** and the drain electrodes **124** and **134** of the transistors TRd and TRs are formed by masking with a fifth mask (not shown).

[0051] The openings H1 and H2 of the third insulating layer **105** are buried by the source electrodes **123** and **133** and the drain electrodes **124** and **134** that are formed as a single layer of multiple layers. The source electrodes **123** and **133** and the drain electrodes **124** and **134** are respectively in contact with the source regions and the drain regions of the active layers **122** and **132** through the openings H2 and H1. The source electrodes **123** and **133** and the drain electrodes **124** and **134** may be formed of a conductive material or by patterning a third conductive layer including, for example, a metal such as Cr, Pt, Ru, Au, Ag, Mo, Al, W, Cu, or AlNd, or a conductive oxide such as ITO, GIZO, GZO, AZO, InZnO (IZO), or AlZnO (AZO).

[0052] Also, the third capacitor electrode **145** of the capacitor Cst may be formed by patterning the third conductive layer at the same time the source electrodes **123** and **133** and the drain electrodes **124** and **134** are formed by patterning.

[0053] Although not shown in the drawings, the data line DL and the driving voltage supply line ELVDD may be formed at the same time when the source electrodes **123** and **133**, the drain electrodes **124** and **134**, and the third capacitor electrode **145** are formed.

[0054] Subsequently, referring to FIG. 7, a fourth insulating layer **106** is stacked on the substrate **101**, on which the source electrodes **123** and **133** and the drain electrodes **124** and **134** and the third capacitor electrode **145** are formed. Also, an opening H3 exposing a part of the drain electrode **134** of the driving transistor TRd is formed by masking with a sixth mask (not shown).

[0055] The fourth insulating layer **106** may be formed of at least one organic insulation material selected from the group of polyimide, polyamide, acrylic resin, benzocyclobutene, and phenol resin, or an inorganic insulation material, such as SiN_x . The fourth insulating layer **106** may be formed by alternating organic insulation materials and inorganic insulation materials. The fourth insulating layer **106** may have one of various structures such as a single layer structure or a double or multi-layered structure.

[0056] Next, as shown in FIG. 8, the pixel electrode **151** of the organic light-emitting layer EL and the fourth capacitor

electrode **147** of the capacitor Cst are formed on the fourth insulating layer **106** by masking with a seventh mask (not shown).

[0057] A transparent conductive layer is stacked on the fourth insulating layer **106**, and the transparent conductive layer is patterned to form the pixel electrode **151**. The transparent conductive layer may include at least one selected from the group of ITO, IZO, ZnO, In₂O₃, IGO, and AZO.

[0058] The pixel electrode **151** is in contact with one of the source electrode **133** and the drain electrode **134** of the driving transistor TRd through the opening H3 of the fourth insulating layer **106**. In an embodiment shown in FIG. 8, the pixel electrode **151** is in contact with the drain electrode **134**.

[0059] Referring to FIG. 9, a fifth insulating layer **107** is stacked on the pixel electrode **151** and the fourth capacitor electrode **147**, and an opening H4 exposing a part of the pixel electrode **151** is formed by masking with an eighth mask (not shown).

[0060] The fifth insulating layer **107** may be formed of at least one organic insulation material selected from the group of polyimide, polyamide, acrylic resin, benzocyclobutene, and phenol resin, or at least one inorganic insulation material selected from the group of SiO₂, SiN_x, Al₂O₃, CuO_x, Tb₄O₇, Y₂O₃, Nb₂O₅, and Pr₂O₃. Also, the fifth insulating layer **107** may include alternating layers of organic insulation materials and inorganic insulation materials. The fifth insulating layer **107** serves as a pixel-defining layer which defines a pixel.

[0061] Next, as shown in FIG. 10, an interlayer **153**, including an emission layer, is formed on the pixel electrode **151**, and a counter electrode **155** is formed on an entire surface of the substrate **101** to cover the interlayer **153**.

[0062] The interlayer **153** may be formed with an emissive layer (EML) and at least one functional layer, such as a hole transport layer (HTL), a hole injection layer (HIL), an electron transport layer (ETL), or an electron injection layer (EIL), that are stacked in a single or combined structure. The interlayer **153** may be formed of a small molecule material or a polymer organic material. When the interlayer **153** emits each of red, green, and blue lights, the EML may be patterned into a red EML, a green EML, and a blue EML, according to a red sub-pixel, a green sub-pixel, and a blue sub-pixel, respectively. When the interlayer **153** emits white light, the EML may have a multi-layer structure where a red EML, a green EML, and a blue EML are stacked, or a single layer structure including a red emission material, a green emission material, and a blue emission material.

[0063] The counter electrode **155** may be formed as a common electrode by deposition on the entire surface of the substrate **101**. In the organic light-emitting display device according to an embodiment, the pixel electrode **151** is used as an anode, and the counter electrode **155** is used as a cathode, or vice versa.

[0064] According to an embodiment, the scan line SL formed of a low resistance wire and gate electrodes of TFTs are formed apart on different layers with an insulating layer therebetween. In this regard, the gate electrode of the TFT may be relatively thinner compared to the case when all of the scan line SL and the gate electrodes of TFTs are formed of a low resistance wire, and accordingly, a thickness of a gate insulating layer between the gate electrodes and the active layer may be thin. Thus, RC load of scan lines and a size of a TFT may be reduced, and thus an aperture ratio of a pixel may be increased. Also, according to an embodiment, the capacitor Cst may be formed as a triple capacitor with the first to

fourth capacitor electrodes **141** to **147**, thus an area of the capacitor Cst may be reduced while capacitance thereof is increased.

[0065] FIG. 11 is a plan view of a single pixel of an organic light-emitting display device according to another embodiment. The pixel shown in FIG. 11 is different from the pixel shown in FIG. 1 in that the number of masking process is less than the embodiment of FIG. 1 by forming a double capacitor having a pixel electrode, a gate electrode, and one electrode of the capacitor with the same material on the same layer.

[0066] The organic light-emitting display device according to the present embodiment includes a plurality of scan lines SL and a plurality of data lines DL on a substrate **201**, and a plurality of pixels PX each located at an intersection region of the scan line SL and the data line DL. Referring to FIG. 11, each of the pixels PX includes an organic light-emitting diode EL for realizing colors in response to a data signal, a driving transistor TRd for applying driving current according to the data signal to the organic light-emitting diode EL, a switching transistor TRs that turns on/off the driving transistor TRd by transmitting the data signal according to a scan signal, and a capacitor Cst for storing voltage that corresponds to the data signal. Here, the pixel PX may further include a plurality of thin film transistors TFTs and capacitors to compensate for a threshold voltage of the driving transistor TRd.

[0067] The switching transistor TRs includes a gate electrode **221** on a layer above the scan line SL and on the same layer as the pixel electrode **251**, an active layer **222** on the gate electrode **221**, and source and drain electrodes **223** and **224** that are electrically connected to two terminal ends of the active layer **222** through contact holes. The gate electrode **221** is electrically connected to the scan line SL through contact holes. One of the source and drain electrodes **223** and **224** is electrically connected to the data line DL and the other is electrically connected to a second capacitor electrode **243** of the capacitor Cst through contact holes. One of the source and drain electrodes **223** and **224** that is electrically connected to the data line DL may be extended from and integrated with the data line DL.

[0068] The driving transistor TRd includes a gate electrode **231** on a layer above the scan line SL and on the same layer as the pixel electrode **251**, an active layer **232** on the gate electrode **231**, and source and drain electrodes **233** and **234** that are electrically connected to the two terminal ends of the active layer **232** through contact holes. The gate electrode **231** is electrically connected to a third capacitor electrode **245** of the capacitor Cst through contact holes. One of the source and drain electrodes **233** and **234** is electrically connected to a driving voltage supply line ELVDD, and the other is electrically connected to a pixel electrode **251** of the organic light-emitting diode EL through contact holes. One of the source and drain electrodes **233** and **234** that is electrically connected to a driving voltage supply line ELVDD may be extended from and integrated with the driving voltage supply line ELVDD.

[0069] The capacitor Cst includes a first capacitor electrode **241** on the same layer as the scan line SL, the second capacitor electrode **243** on the first capacitor electrode **241** and formed on the same layer as the gate electrodes **221** and **231** and the pixel electrode **251** of the organic light-emitting device EL, and a third capacitor electrode **245** on the second capacitor electrode **243** and formed on the same layer as source and drain electrodes **223** and **224** and **233** and **234**. The first capacitor electrode **241** and the third capacitor electrode **245**

are electrically connected through contact holes. The second capacitor electrode **243** may be extended from and may be integrated with the pixel electrode **251**.

[0070] FIGS. **12** to **18** are cross-sectional views of FIG. **11** cut through lines E-E', F-F', G-G', and H-H' to describe stages in a method of manufacturing the organic light-emitting display device, according to an embodiment.

[0071] Referring to FIG. **12**, a buffer layer **202** is formed on the substrate **201**, a first mask (not shown) is formed on the buffer layer **202**, and the scan line SL and the first capacitor electrode **241** of the capacitor Cst are formed on the buffer layer **202** by masking with a first mask (not shown).

[0072] The substrate **201** may be formed of a transparent glass material, mainly including SiO₂. However, the substrate **201** of the present embodiment is not limited thereto, and may be formed of various materials such as, for example, transparent plastic material or metal material.

[0073] The buffer layer **202** serves as a barrier layer and/or a blocking layer to prevent diffusion of impurity ions and permeation of moisture or external air, and to planarize a surface of the substrate **201**. The buffer layer **202** may be formed using SiO₂ and/or SiN_x by various deposition methods such as PECVD, APCVD, and LPCVD.

[0074] The scan line SL and the first capacitor electrode **241** may be formed simultaneously by stacking a first conductive layer on the substrate **201** and patterning the first conductive layer. The first conductive layer includes at least one metal material from the group of aluminum (Al), platinum (Pt), palladium (Pd), silver (Ag), magnesium (Mg), gold (Au), nickel (Ni), neodymium (Nd), iridium (Ir), chromium (Cr), lithium (Li), calcium (Ca), molybdenum (Mo), titanium (Ti), tungsten (W), and copper (Cu), and the first conductive layer may be formed as a single layer or multiple layers. A first conductive layer including a metal material with a low resistance, such as Al or Cu, is preferred but the first conductive layer may include other metal materials to form the first conductive layer as a single layer or multiple layers with an increased thickness.

[0075] Next, as shown in FIG. **13**, a first insulating layer **203** is formed on the substrate **201**, and then, the pixel electrode **251** of the organic light-emitting diode EL, the gate electrode **231** of the driving transistor TRd, the gate electrode **221** of the switching transistor TRs, and the second capacitor electrode **243** of the capacitor Cst are formed on the first insulating layer **203** by masking with a second mask (not shown). The second capacitor electrode **243** has an overlapping area with the first capacitor electrode **241**.

[0076] The first insulating layer **203** may be formed of at least one organic insulation material selected from the group of polyimide, polyamide, acrylic resin, benzocyclobutene, and phenol resin, or at least one inorganic insulation material selected from the group of SiO₂, SiN_x, Al₂O₃, CuO_x, Tb₄O₇, Y₂O₃, Nb₂O₅, and Pr₂O₃. Also, the first insulating layer **203** may include alternating layers of organic insulation materials and inorganic insulation materials.

[0077] The gate electrodes **221** and **231**, the second capacitor electrode **243**, and the pixel electrode **251** may be formed simultaneously by depositing a second conductive layer on the first insulating layer **203** and patterning the second conductive layer. The second conductive layer may be a transparent conductive electrode including at least one transparent conductive material selected from the group of ITO, IZO, ZnO, In₂O₃, IGO, and AZO.

[0078] Referring to FIG. **14**, the active layers **222** and **232** are formed on the gate electrodes **221** and **231**, the second capacitor electrode **243**, and the pixel electrode **251** by masking with a third mask (not shown).

[0079] A second insulating layer **204** and an oxide semiconductor are deposited on the substrate **201**, on which the gate electrodes **221** and **231**, the second capacitor electrode **243**, and the pixel electrode **251** are formed, and then, the oxide semiconductor is patterned to form the active layers **222** and **232**.

[0080] The second insulating layer **204** serves as a gate insulating layer and may be formed of an inorganic insulation material, such as SiN_x or SiO_x, or an organic insulation material. According to an embodiment, the scan line SL formed by the first conductive layer and the gate electrodes **221** and **231** formed by the second conductive layer may be formed apart, the gate electrodes **221** and **231** may be formed thinner than the scan line SL, which is a wire with low resistance, and thus a thickness of the second insulating layer **204** may also be thin. Therefore, a size of a TFT may be reduced.

[0081] The active layers **222** and **232** each provide a channel region, a source region, and a drain region, wherein the channel region overlaps with the gate electrodes **221** and **231**. The oxide semiconductor may contain at least one element selected from the group of gallium (Ga), indium (In), stannum (Sn), zirconium (Zr), hafnium (Hf), and vanadium (V). For example, the oxide semiconductor may include at least one selected from the group of ZnO, SnO₂, In₂O₃, Zn₂SnO₄, Ga₂O₃, and HfO₂. Also, the active layer **132** may be formed of a transparent oxide semiconductor. Examples of the transparent oxide semiconductor include, for example, Zn oxide, Sn oxide, Ga—In—Zn oxide, In—Zn oxide, and In—Sn oxide, but are not limited thereto.

[0082] Referring to FIG. **15**, a third insulating layer **205** is stacked on the active layers **222** and **232**, and openings H5 and H6 exposing a part of the source and drain regions of the active layers **222** and **232** and an opening H7 exposing a part of the pixel electrode **251** are formed by masking with a fourth mask (not shown). The opening H7 is formed by etching the second insulating layer **204** and the third insulating layer **205**.

[0083] The third insulating layer **205** serves as an inter-layer dielectric and may be formed of an inorganic insulation material, such as SiN_x or SiO_x, or an organic insulation material.

[0084] Next, referring to FIG. **16**, the source electrode **233** and the drain electrode **234** of the driving transistor TRd, the source electrode **223** and the drain electrode **224** of the source transistor TRs, and the third capacitor electrode **245** of the capacitor Cst are formed by masking with a fifth mask (not shown).

[0085] The openings H5, H6, and H7 of the third insulating layer **205** are buried by a third conductive layer that is stacked on the third insulating layer **205**. Then, the third conductive layer is patterned to form the source electrodes **223** and **233**, the drain electrodes **224** and **234**, and the third capacitor electrode **245**. Here, one of the source electrode **233** and the drain electrode **234** of the driving transistor TRd may be in contact with a part of the pixel electrode **251**. In the embodiment shown in FIG. **16**, the drain electrode **234** is in contact with a part of the pixel electrode **251**. The third conductive layer may include, for example, a metal such as Cr, Pt, Ru, Au, Ag, Mo, Al, W, Cu, or AlNd, or a conductive oxide such as

ITO, GIZO, GZO, AZO, InZnO (IZO), or AlZnO (AZO) and may be formed as a single layer or multiple layers.

[0086] Also, the third capacitor electrode **245** of the capacitor Cst may be formed by patterning the third conductive layer at the same time the source electrodes **223** and **233** and the drain electrodes **224** and **234** are formed by patterning.

[0087] Although not shown in the drawings, the data line DL and the driving voltage supply line ELVDD may be formed at the same time when the source electrodes **223** and **233**, the drain electrodes **224** and **234**, and the third capacitor electrode **245** are formed.

[0088] Subsequently, referring to FIG. 17, a fourth insulating layer **206** is stacked on the substrate **201**, on which the source electrodes **223** and **233**, the drain electrodes **224** and **234**, and the third capacitor electrode **245** are formed. Also, an opening H8 exposing a part of the pixel electrode **251** is formed in the fourth insulating layer **206** by masking with a sixth mask (not shown).

[0089] The fourth insulating layer **206** may be formed of at least one organic insulation material selected from the group of polyimide, polyamide, acrylic resin, benzocyclobutene, and phenol resin, or at least one inorganic insulation material selected from the group of SiO₂, SiN_x, Al₂O₃, CuO_x, Tb₄O₇, Y₂O₃, Nb₂O₅, and Pr₂O₃. Also, the fourth insulating layer **206** may have alternating layers of organic insulation materials and inorganic insulation materials. The fourth insulating layer **206** serves as a pixel-defining layer which defines a pixel.

[0090] Next, as shown in FIG. 18, an interlayer **253**, including an emission layer, is formed on the pixel electrode **251**, and a counter electrode **255** is formed on an entire surface of the substrate **201** to cover the interlayer **253**.

[0091] The interlayer **253** may be formed with an EML and at least one functional layer, such as an HTL, an HIL, an ETL, or an EIL, that are stacked in a single or combined structure. The interlayer **253** may be formed of a small molecule or a polymer organic material. When the interlayer **253** emits each of red, green, and blue lights, the EML may be patterned into a red EML, a green EML, and a blue EML, according to a red sub-pixel, a green sub-pixel, and a blue sub-pixel, respectively. When the interlayer **253** emits white light, the EML may have a multi-layer structure where a red EML, a green EML, and a blue EML are stacked, or a single layer structure including a red emission material, a green emission material, and a blue emission material.

[0092] The counter electrode **255** may be formed as a common electrode by deposition on the entire surface of the substrate **201**. In the organic light-emitting display device according to an embodiment, the pixel electrode **251** is used as an anode, and the counter electrode **255** is used as a cathode, or vice versa.

[0093] By way of summation and review, according to embodiments, the scan lines SL formed of a low resistance wire and gate electrodes of TFTs are formed apart on different layers with an insulating layer therebetween. In this regard, the gate electrode of the TFT may be relatively thinner compared to the case when all of the scan line SL and the gate electrodes of TFTs are formed of a low resistance wire, and accordingly, a thickness of a gate insulating layer between the gate electrodes and the active layer may be thin. Thus, RC load of scan lines and a size of a TFT may be reduced, and thus an aperture ratio of a pixel may be increased. Also, according to an embodiment, the capacitor Cst may be formed as a double capacitor with the first to third capacitor electrodes

241 to **245**, thus an area of the capacitor Cst may be reduced while capacitance thereof is increased.

[0094] In contrast, a conventional display device has scan lines and TFTs formed with the same low resistance wire. In this regard, however, the thicknesses of the gate electrodes and a gate insulating layer are increased. Thus an on-current of the TFT is reduced, a size of the TFT is increased, the number of parasitic capacitors is increased, and an area of a storage capacitor is increased. Accordingly, an aperture ratio of the conventional display device is reduced.

[0095] Although embodiments of organic light-emitting display devices have been described, the present invention is not limited thereto. Also, it would have been obvious to use a method of constructing a wire that separates scan lines from gate electrodes of TFTs and forms the scan lines as one electrode of a capacitor in various display devices including liquid display devices.

[0096] As described above, according to the one or more of the above embodiments, a wire forming scan lines SL and gate electrodes of TFTs are formed apart, thus RC load of scan lines, a size of a TFT, and an area of a storage capacitor may be reduced, and accordingly, an aperture ratio of a display device may be improved.

[0097] While the present invention has been particularly shown and described with reference to exemplary embodiments thereof, it will be understood by those of ordinary skill in the art that various changes in form and details may be made therein without departing from the spirit and scope of the present invention as defined by the following claims.

What is claimed is:

1. An organic light-emitting display device including a plurality of scan lines and a plurality of data lines, and a plurality of pixels each located at an intersection region of the scan line and the data line, wherein the organic light-emitting display device comprises:

a thin film transistor including a gate electrode on a different layer than a scan line, an active layer on the gate electrode, and source and drain electrodes in contact with source and drain regions of the active layer; and
a capacitor including a first capacitor electrode on a same layer as the scan line, a second capacitor electrode on the gate electrode, and a third capacitor electrode on a same layer as the source and drain electrodes.

2. The organic light-emitting display device of claim 1, wherein the active layer is formed of an oxide semiconductor.

3. The organic light-emitting display device of claim 1, wherein a thickness of the gate electrode is thinner than a thickness of the scan line.

4. The organic light-emitting display device of claim 1, wherein the scan line is a low resistance wire.

5. The organic light-emitting display device of claim 1, wherein the capacitor further comprises a fourth capacitor electrode on the third capacitor electrode.

6. The organic light-emitting display device of claim 5, further comprising a pixel electrode on the source and drain electrodes and on a same layer as the fourth capacitor electrode.

7. The organic light-emitting display device of claim 5, further comprising:

a first insulating layer between the first capacitor electrode and the second capacitor electrode;
a second insulating layer and a third insulating layer between the second capacitor electrode and the third capacitor electrode; and

a fourth insulating layer between the third capacitor electrode and the fourth capacitor electrode.

8. The organic light-emitting display device of claim 1, further comprising a pixel electrode on the same layer as the gate electrode and the second capacitor electrode.

9. The organic light-emitting display device of claim 8, further comprising:

a first insulating layer between the first capacitor electrode and the second capacitor electrode; and

a second insulating layer and a third insulating layer between the second capacitor electrode and the third capacitor electrode.

10. The organic light-emitting display device of claim 1, wherein the scan line and the gate electrode are electrically connected through contact holes formed in an insulating layer between the scan line and the gate electrode.

11. A method of manufacturing an organic light-emitting display device, the method comprising:

forming a first capacitor electrode on a same layer as a scan line;

forming a first insulating layer on the first capacitor electrode;

forming a gate electrode and a second capacitor electrode on the first insulating layer;

forming a second insulating layer on the gate electrode and the second capacitor electrode;

forming an active layer that overlaps the gate electrode on the second insulating layer;

forming a third insulating layer on the active layer, the third insulating layer including openings which expose a part of source and drain regions of the active layer; and

forming a third capacitor electrode and source and drain electrodes on the third insulating layer, the source and

drain electrodes being in contact with the source and drain regions through the openings.

12. The method of claim 11, wherein the active layer is formed of an oxide semiconductor.

13. The method of claim 11, wherein a thickness of the gate electrode is thinner than a thickness of the scan line.

14. The method of claim 11, wherein the scan line is a low resistance wire.

15. The method of claim 11, further comprising:

forming a fourth insulating layer on the source and drain electrodes; and

forming a fourth capacitor electrode on the fourth insulating layer.

16. The method of claim 15, further comprising forming a pixel electrode on a same layer as the fourth capacitor electrode.

17. The method of claim 16, further comprising forming a fifth insulating layer, which has an opening that exposes a part of the pixel electrode, on the pixel electrode and the fourth capacitor electrode.

18. The method of claim 11, further comprising forming a pixel electrode on a same layer as the gate electrode and the second capacitor electrode.

19. The method of claim 18, further comprising forming a fourth insulating layer, which has an opening that exposes a part of the pixel electrode, on the pixel electrode, which is partially exposed by the opening included in the second insulating layer and the third insulating layer, the third capacitor electrode, and the source and drain electrodes.

20. The method of claim 11, further comprising forming an electrode pattern that electrically connects the scan line and the gate electrode through contact holes formed in an insulating layer between the scan line and the gate electrode.

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专利名称(译)	有机发光显示装置及其制造方法		
公开(公告)号	US20140097411A1	公开(公告)日	2014-04-10
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摘要(译)

有机发光显示装置可包括多条扫描线，多条数据线和位于扫描线 & 数据线的交叉区域的多个像素，其中有机发光显示装置包括：薄膜晶体管，包括与扫描线不同的层上的栅电极，栅电极上的有源层，以及有源层的源区和漏区接触的源电极和漏电极，以及包括第一电容器的电容器电极位于与扫描线相同的层上，第二电容器电极位于栅电极上，第三电极位于与源电极和漏电极相同的层上。

